

LT1055S8/LT1056S8

Precision, High Speed, JFET Input Operational Amplifiers

FEATURES

- Guaranteed Offset Voltage 0°C to 70°C
- Low Drift
- Guaranteed Bias Current 70°C Warmed Up
- Guaranteed Slew Rate

APPLICATIONS

- Precision, High Speed Instrumentation
- Logarithmic Amplifiers
- D/A Output Amplifiers
- Photodiode Amplifiers
- Voltage to Frequency Converters
- Frequency to Voltage Converters
- Fast, Precision Sample and Hold

DESCRIPTION

1.5mV Max.

2.2mV Max. 4μV/°C Typ.

400pA Max.

9V/μs Min.

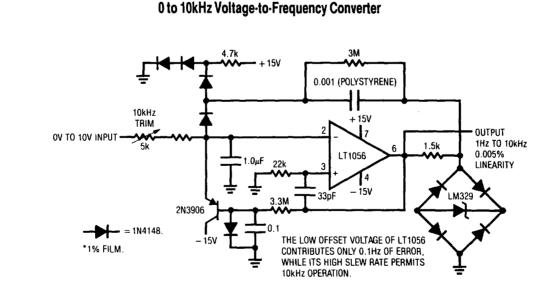
The LT1055/LT1056 JFET input operational amplifiers combine precision specifications with high speed performance.

For the first time in an SO package, $14V/\mu s$ slew rate and 5.5MHz gain-bandwidth product are simultaneously achieved with offset voltage of typically 0.5mV, $4\mu V/^{\circ}C$ drift, and bias currents of 60pA at 70°C.

The 1.5mV maximum offset voltage specification is the best available on any JFET input operational amplifier in the plastic SO package.

The LT1055 and LT1056 are differentiated by their operating currents. The lower power dissipation LT1055 achieves lower bias and offset currents and offset voltage. The additional power dissipation of the LT1056 permits higher slew rate, bandwidth and faster settling time with a slight sacrifice in DC performance.

The voltage to frequency converter shown below is one of the many applications which utilize both the precision and high speed of the LT1055/LT1056.



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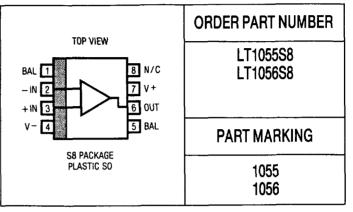


LT1055S8/LT1056S8

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	± 20V
Differential Input Voltage	± 40V
Input Voltage	
Output Short Circuit Duration	
Operating Temperature Range	
Storage Temperature Range	
All Devices	C to 150°C
Lead Temperature (Soldering, 10 sec.)	300°C

PACKAGE/ORDER INFORMATION



ELECTRICAL CHARACTERISTICS $v_s = \pm 15V$, $T_A = 25^{\circ}C$, $v_{CM} = 0V$ unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS		MIN	LT1055S8 LT1056S8 TYP	MAX	UNITS
Vos	Input Offset Voltage (Note 1)				500	1500	μV
los	Input Offset Current	Fully Warmed	Up		5	30	рА
IB	Input Bias Current	Fully Warmed V _{CM} = + 10V	Up		± 30 30	± 100 150	рА рА
	Input Resistance — Differential — Common-Mode	$V_{CM} = -11V to$ $V_{CM} = +8V to$	o +8V +11V		0.4 0.4 0.05		ΤΩ ΤΩ ΤΩ
	Input Capacitance				4		pF
e _n	Input Noise Voltage	0.1Hz to 10Hz	LT1055 LT1056		2.5 3.5		μVp-p μVp-p
e _n	Input Noise Voltage Density	$f_o = 10Hz$ (Note $f_o = 1kHz$ (Note			35 15	70 22	nV/√Hz nV/√Hz
i _n	Input Noise Current Density	f _o = 10Hz, 1kH	z (Note 3)		2.5	10	fA/√Hz
A _{VOL}	Large Signal Voltage Gain	$V_0 = \pm 10V$	$R_L = 2k$ $R_L = 1k$	120 100	400 300		V/mV V/mV
	Input Voltage Range			± 11	± 12		V
CMRR	Common-Mode Rejection Ratio	$V_{CM} = \pm 11V$		83	98		dB
PSRR	Power Supply Rejection Ratio	$V_{\rm S} = \pm 10V$ to	± 18V	88	104		dB
VOUT	Output Voltage Swing	$R_L = 2k$		± 12	± 13.2		v
SR	Slew Rate		LT1055 LT1056	7.5 9.0	12 14		V/μs V/μs
GBW	Gain-Bandwidth Product	f = 1MHz	LT1055 LT1056		4.5 5.5		MHz MHz
Is	Supply Current		LT1055 LT1056		2.8 5.0	4.0 7.0	mA mA
	Offset Voltage Adjustment Range	R _{POT} = 100k			±5		mV





LT1055S8/LT1056S8

ELECTRICAL CHARACTERISTICS $V_{S} = \pm 15V$, $V_{CM} = 0V$, $0^{\circ}C \le T_{A} \le 70^{\circ}C$, unless otherwise noted.

				LT1055S8/1056S8			
SYMBOL	PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS
V _{os}	Input Offset Voltage (Note 1)		•		800	2200	μV
	Average Temperature Coefficient of Input Offset Voltage		•		4	15	µV/°C
los	Input Offset Current	Warmed Up $T_A = 70^{\circ}C$	•		18	150	рА
1 _B	Input Bias Current	Warmed Up $T_A = 70^{\circ}C$	•		±60	± 400	рА
A _{VOL}	Large Signal Voltage Gain	$V_0 = \pm 10V, R_1 = 2k$	•	60	250		V/mV
CMRR	Common-Mode Rejection Ratio	$V_{CM} = \pm 10.5V$	•	82	98		dB
PSRR	Power Supply Rejection Ratio	$V_{\rm S} = \pm 10V$ to $\pm 18V$	•	87	103		dB
VOUT	Output Voltage Swing	$R_1 = 2k$	•	± 12	± 13.1		V

The \bullet denotes the specifications which apply over the full operating temperature range.

Note 1: Offset voltage is measured under two different conditions: (a) approximately 0.5 seconds after application of power; (b) at $T_A = 25^{\circ}C$

only, with the chip heated to approximately 38° C for the LT1055 and to 45° C for the LT1056, to account for chip temperature rise when the device is fully warmed up.

Note 2: This parameter is tested on a sample basis only.

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contribution of current noise. **Note 4:** Offset voltage drift with temperature is practically unchanged when the offset voltage voltage is trimmed to zero with a 100k potentiometer be-

Note 3: Current noise is calculated from the formula: $i_n = (2ql_B)^{\frac{1}{2}}$, where $q = 1.6 \times 10^{-19}$ coulomb. The noise of source resistors up to 1G Ω swamps the

tween the balance terminals and the wiper tied to V+.



